

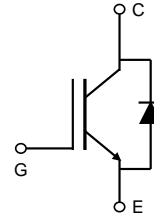
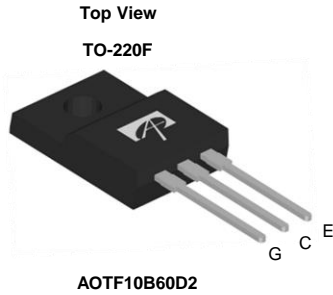


**General Description**

The AlphaIGBT™ line of products offers best-in-class performance in conduction and switching losses, with robust short circuit capability. They are designed for ease of paralleling, minimal gate spike under high dV/dt conditions and resistance to oscillations. The co-packaged soft diode is optimized to minimize losses in motor control applications.

**Product Summary**

$V_{CE}$	600V
$I_C$ ( $T_C=100^\circ\text{C}$ )	10A
$V_{CE(sat)}$ ( $T_J=25^\circ\text{C}$ )	1.55V



**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	AOTF10B60D2	Units
Collector-Emitter Voltage	$V_{CE}$	600	V
Gate-Emitter Voltage	$V_{GE}$	$\pm 20$	V
Continuous Collector Current <sup>A</sup>	$I_C$	$T_C=25^\circ\text{C}$	23 <sup>B</sup>
		$T_C=100^\circ\text{C}$	10
Pulsed Collector Current, Limited by $T_{Jmax}$	$I_{CM}$	20	A
Turn off SOA, $V_{CE} \leq 600\text{V}$ , Limited by $T_{Jmax}$	$I_{LM}$	20	A
Continuous Diode Forward Current <sup>A</sup>	$I_F$	$T_C=25^\circ\text{C}$	23 <sup>B</sup>
		$T_C=100^\circ\text{C}$	10
Diode Pulsed Current, Limited by $T_{Jmax}$	$I_{FM}$	20	A
Short circuit withstanding time $V_{GE} = 15\text{V}$ , $V_{CE} \leq 400\text{V}$ , Delay between short circuits $\geq 1.0\text{s}$ , $T_C=25^\circ\text{C}$	$t_{SC}$	10	$\mu\text{s}$
Power Dissipation	$P_D$	$T_C=25^\circ\text{C}$	31.2
		$T_C=100^\circ\text{C}$	12.5
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	$T_L$	300	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	AOTF10B60D2	Units
Maximum Junction-to-Ambient	$R_{\theta JA}$	65	$^\circ\text{C/W}$
Maximum IGBT Junction-to-Case	$R_{\theta JC}$	4	$^\circ\text{C/W}$
Maximum Diode Junction-to-Case	$R_{\theta JC}$	4	$^\circ\text{C/W}$

Note A: With 50% duty cycle and 200 $\mu\text{s}$  pulse width

Note B:  $I_C$  limited by package limitation

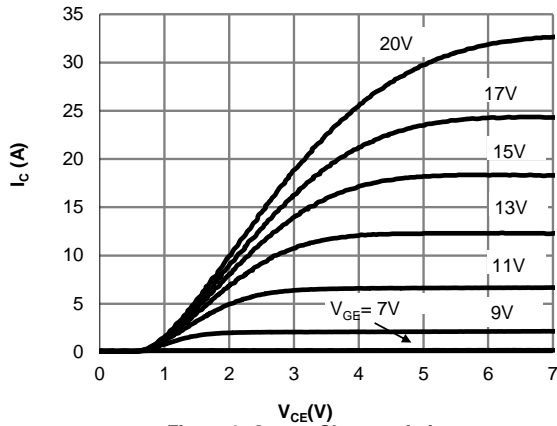
**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
<b>STATIC PARAMETERS</b>							
$BV_{CES}$	Collector-Emitter Breakdown Voltage	$I_C=1\text{mA}$ , $V_{GE}=0\text{V}$ , $T_J=25^\circ\text{C}$	600	-	-	V	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{GE}=15\text{V}$ , $I_C=5\text{A}$	$T_J=25^\circ\text{C}$	-	1.55	1.8	V
			$T_J=125^\circ\text{C}$	-	1.78	-	
			$T_J=150^\circ\text{C}$	-	1.85	-	
$V_F$	Diode Forward Voltage	$V_{GE}=0\text{V}$ , $I_C=5\text{A}$	$T_J=25^\circ\text{C}$	-	1.46	1.75	V
			$T_J=125^\circ\text{C}$	-	1.36	-	
			$T_J=150^\circ\text{C}$	-	1.3	-	
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$V_{CE}=V_{GE}$ , $I_C=1\text{mA}$	-	6	-	V	
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{CE}=600\text{V}$ , $V_{GE}=0\text{V}$	$T_J=25^\circ\text{C}$	-	-	10	$\mu\text{A}$
			$T_J=125^\circ\text{C}$	-	-	100	
			$T_J=150^\circ\text{C}$	-	-	500	
$I_{GES}$	Gate-Emitter Leakage Current	$V_{CE}=0\text{V}$ , $V_{GE}=\pm 20\text{V}$	-	-	$\pm 100$	nA	
$g_{FS}$	Forward Transconductance	$V_{CE}=20\text{V}$ , $I_C=5\text{A}$	-	2.3	-	S	
<b>DYNAMIC PARAMETERS</b>							
$C_{ies}$	Input Capacitance	$V_{GE}=0\text{V}$ , $V_{CE}=25\text{V}$ , $f=1\text{MHz}$	-	367	-	pF	
$C_{oes}$	Output Capacitance		-	34	-	pF	
$C_{res}$	Reverse Transfer Capacitance		-	1.47	-	pF	
$Q_g$	Total Gate Charge	$V_{GE}=15\text{V}$ , $V_{CE}=480\text{V}$ , $I_C=5\text{A}$	-	9.4	-	nC	
$Q_{ge}$	Gate to Emitter Charge		-	3.15	-	nC	
$Q_{gc}$	Gate to Collector Charge		-	3.6	-	nC	
$I_{C(SC)}$	Short circuit collector current, Max. 1000 short circuits, Delay between short circuits $\geq 1.0\text{s}$	$V_{GE}=15\text{V}$ , $V_{CE}=400\text{V}$ , $R_G=60\Omega$	-	21	-	A	
$R_g$	Gate Resistance	$V_{GE}=0\text{V}$ , $V_{CE}=0\text{V}$ , $f=1\text{MHz}$	-	3	-	$\Omega$	
<b>SWITCHING PARAMETERS, (Load Inductive, T<sub>J</sub>=25°C)</b>							
$t_{D(on)}$	Turn-On Delay Time	$T_J=25^\circ\text{C}$ $V_{GE}=15\text{V}$ , $V_{CE}=400\text{V}$ , $I_C=5\text{A}$ , $R_G=60\Omega$ , Parasitic Inductance=100nH	-	12	-	ns	
$t_r$	Turn-On Rise Time		-	15	-	ns	
$t_{D(off)}$	Turn-Off Delay Time		-	83	-	ns	
$t_f$	Turn-Off Fall Time		-	12	-	ns	
$E_{on}$	Turn-On Energy		-	0.14	-	mJ	
$E_{off}$	Turn-Off Energy		-	0.04	-	mJ	
$E_{total}$	Total Switching Energy		-	0.18	-	mJ	
$t_{rr}$	Diode Reverse Recovery Time		$T_J=25^\circ\text{C}$	-	98	-	ns
$Q_{rr}$	Diode Reverse Recovery Charge		$I_F=5\text{A}$ , $dI/dt=200\text{A}/\mu\text{s}$ , $V_{CE}=400\text{V}$	-	0.23	-	$\mu\text{C}$
$I_{rm}$	Diode Peak Reverse Recovery Current		-	-	4.4	-	A
<b>SWITCHING PARAMETERS, (Load Inductive, T<sub>J</sub>=150°C)</b>							
$t_{D(on)}$	Turn-On Delay Time	$T_J=150^\circ\text{C}$ $V_{GE}=15\text{V}$ , $V_{CE}=400\text{V}$ , $I_C=5\text{A}$ , $R_G=60\Omega$ , Parasitic Inductance=100nH	-	10	-	ns	
$t_r$	Turn-On Rise Time		-	16	-	ns	
$t_{D(off)}$	Turn-Off Delay Time		-	108	-	ns	
$t_f$	Turn-Off Fall Time		-	16	-	ns	
$E_{on}$	Turn-On Energy		-	0.18	-	mJ	
$E_{off}$	Turn-Off Energy		-	0.09	-	mJ	
$E_{total}$	Total Switching Energy		-	0.27	-	mJ	
$t_{rr}$	Diode Reverse Recovery Time		$T_J=150^\circ\text{C}$	-	166	-	ns
$Q_{rr}$	Diode Reverse Recovery Charge		$I_F=5\text{A}$ , $dI/dt=200\text{A}/\mu\text{s}$ , $V_{CE}=400\text{V}$	-	0.4	-	$\mu\text{C}$
$I_{rm}$	Diode Peak Reverse Recovery Current		-	-	5.2	-	A

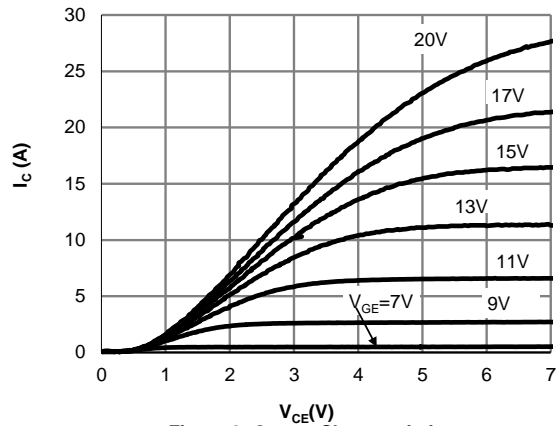
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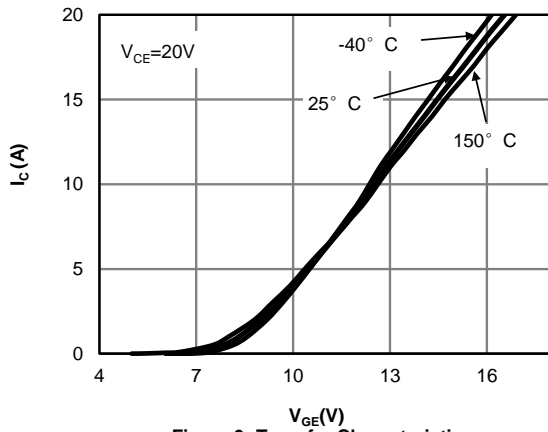
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



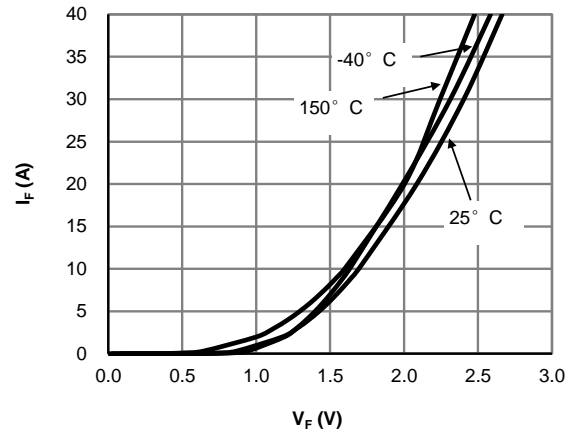
**Figure 1: Output Characteristic**  
( $T_j=25^\circ\text{C}$ )



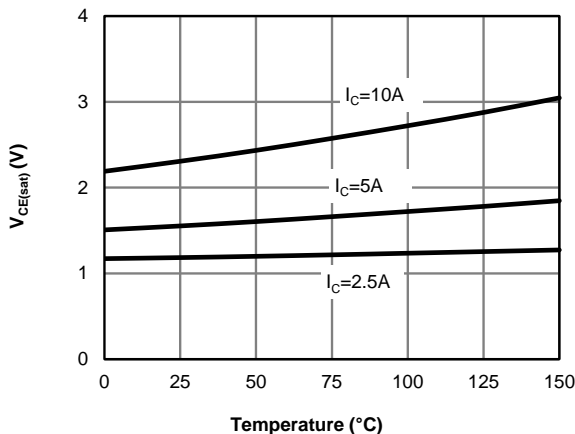
**Figure 2: Output Characteristic**  
( $T_j=150^\circ\text{C}$ )



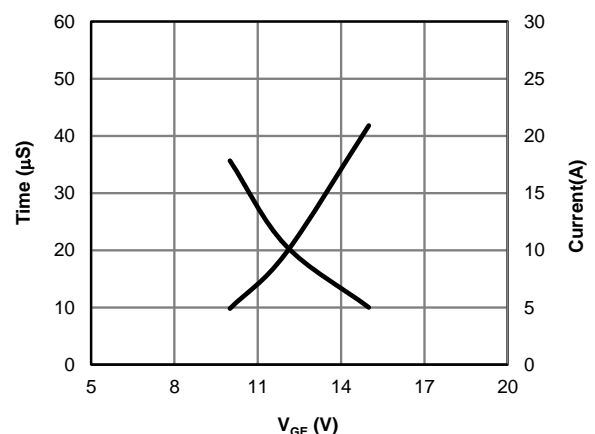
**Figure 3: Transfer Characteristic**



**Figure 4: Diode Characteristic**

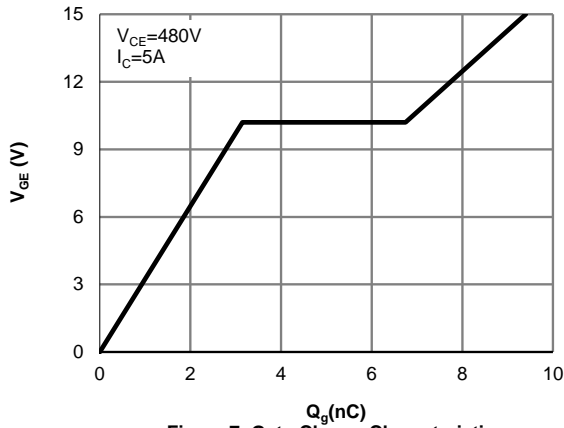


**Figure 5: Collector-Emitter Saturation Voltage vs. Junction Temperature**

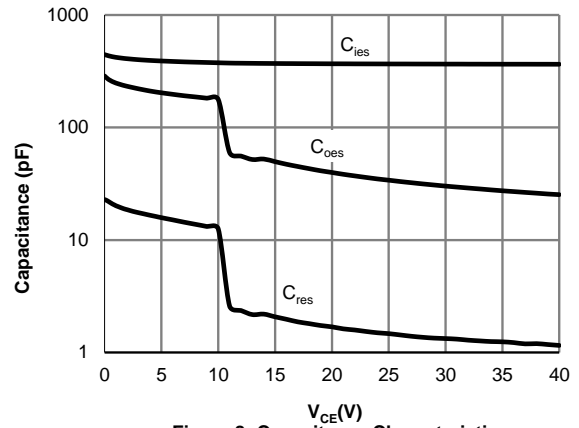


**Figure 6:  $V_{GE}$  vs. Short Circuit Time**  
( $V_{CE}=400\text{V}, T_C=25^\circ\text{C}$ )

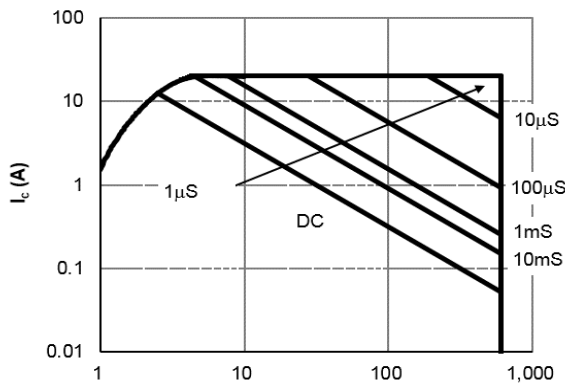
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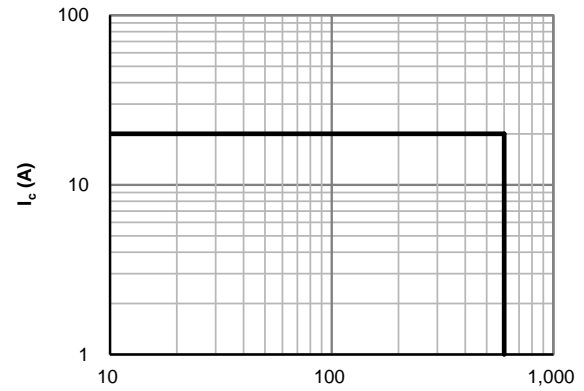
**Figure 7: Gate-Charge Characteristics**



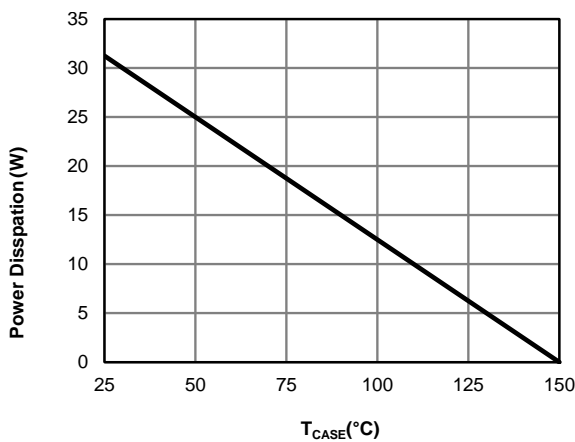
**Figure 8: Capacitance Characteristic**



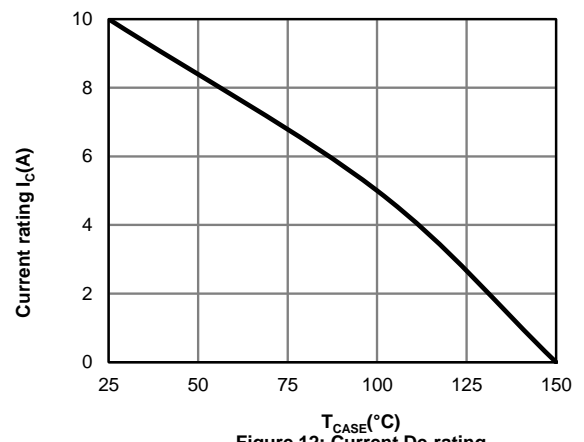
**Figure 9: Forward Bias Safe Operating Area**  
( $T_C=25^\circ\text{C}, V_{GE}=15\text{V}$ )



**Figure 10: Reverse Bias SOA**  
( $T_J=150^\circ\text{C}, V_{GE}=15\text{V}$ )

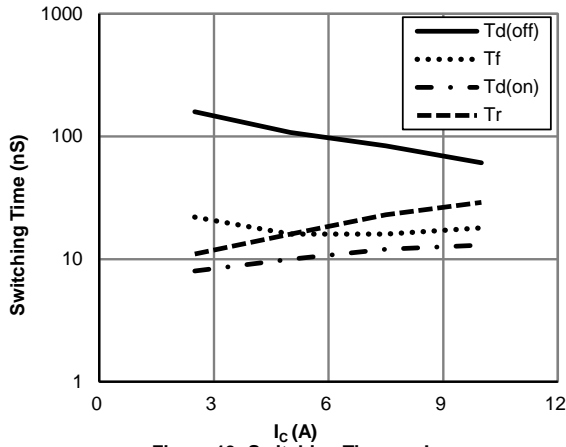


**Figure 11: Power Dissipation as a Function of Case**

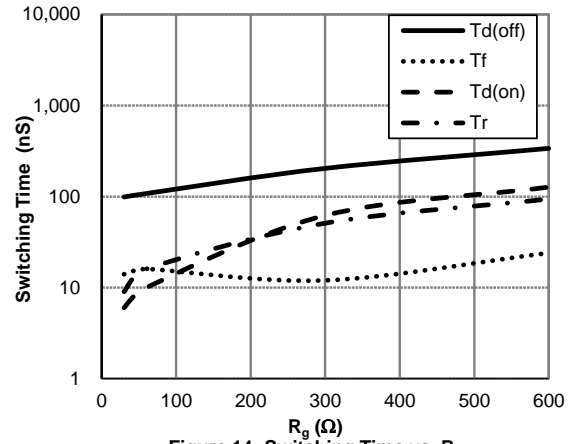


**Figure 12: Current De-rating**

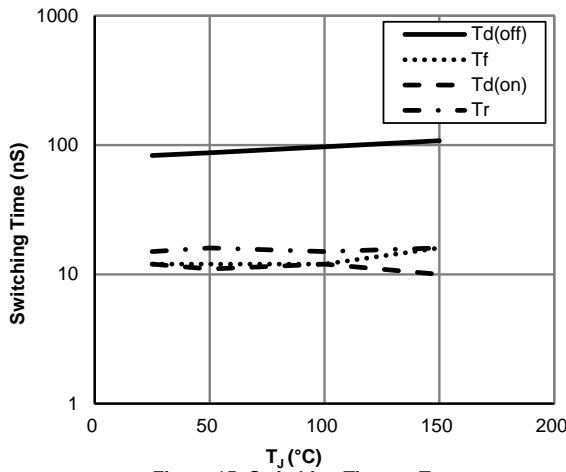
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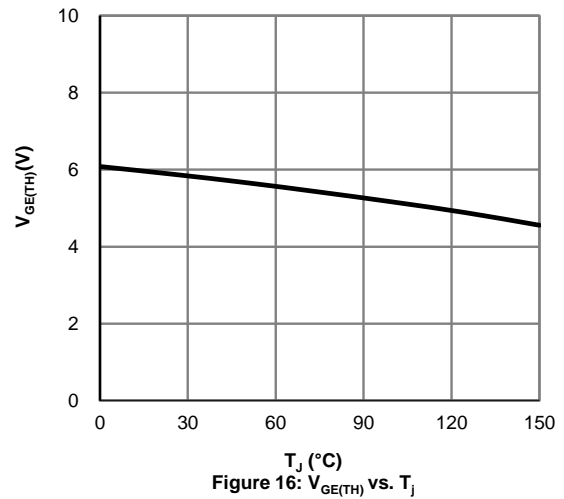
**Figure 13: Switching Time vs.  $I_C$**   
( $T_J=150^\circ\text{C}, V_{GE}=15\text{V}, V_{CE}=400\text{V}, R_g=60\Omega$ )



**Figure 14: Switching Time vs.  $R_g$**   
( $T_J=150^\circ\text{C}, V_{GE}=15\text{V}, V_{CE}=400\text{V}, I_C=5\text{A}$ )

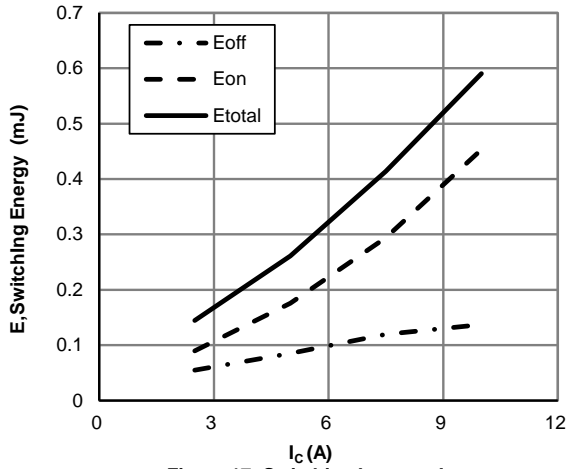


**Figure 15: Switching Time vs.  $T_J$**   
( $V_{GE}=15\text{V}, V_{CE}=400\text{V}, I_C=5\text{A}, R_g=60\Omega$ )

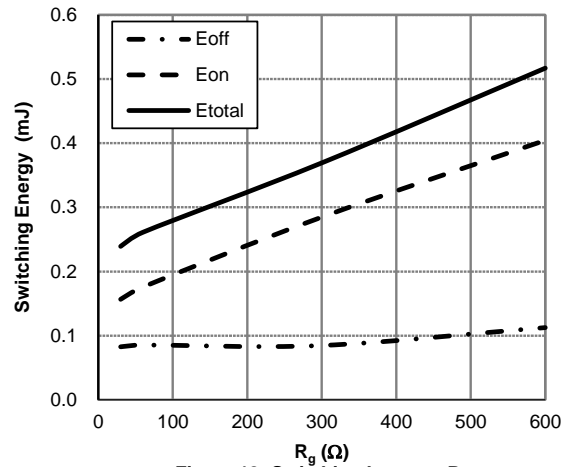


**Figure 16:  $V_{GE(TH)}$  vs.  $T_J$**

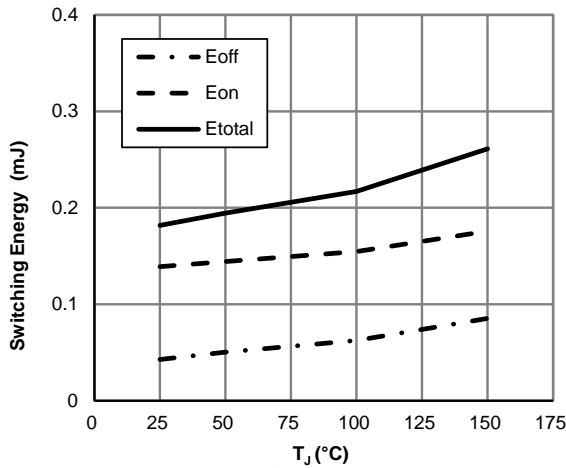
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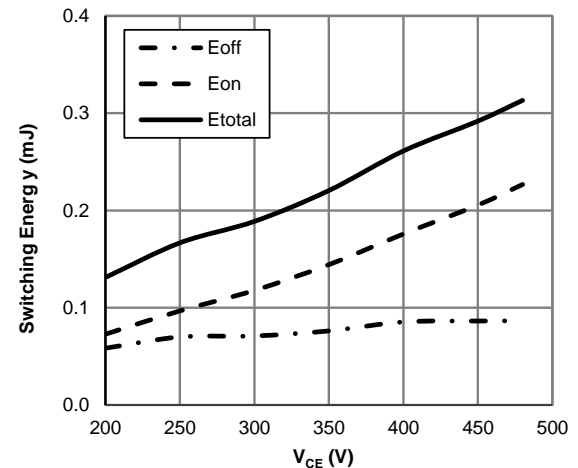
**Figure 17: Switching Loss vs.  $I_C$**   
( $T_J=150^\circ\text{C}, V_{GE}=15\text{V}, V_{CE}=400\text{V}, R_g=60\Omega$ )



**Figure 18: Switching Loss vs.  $R_g$**   
( $T_J=150^\circ\text{C}, V_{GE}=15\text{V}, V_{CE}=400\text{V}, I_C=5\text{A}$ )

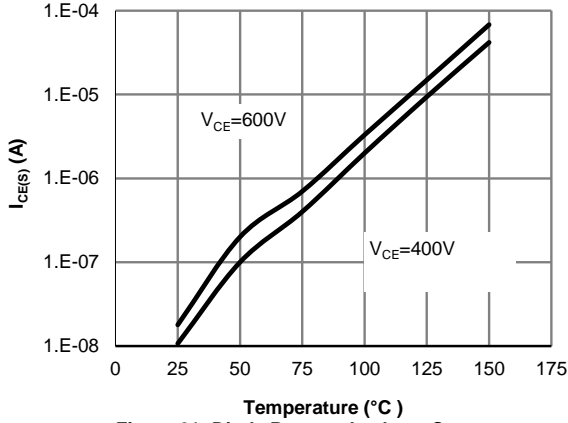


**Figure 19: Switching Loss vs.  $T_J$**   
( $V_{GE}=15\text{V}, V_{CE}=400\text{V}, I_C=5\text{A}, R_g=60\Omega$ )

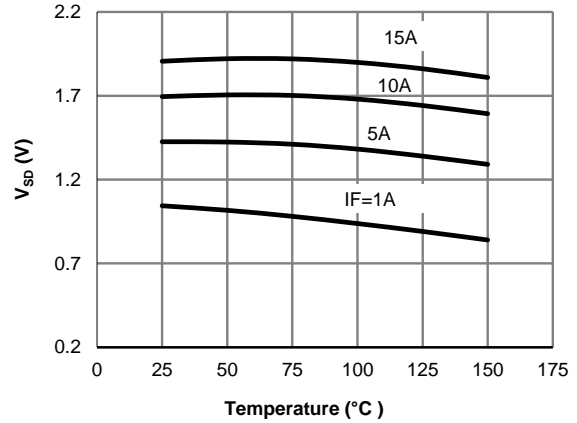


**Figure 20: Switching Loss vs.  $V_{CE}$**   
( $T_J=150^\circ\text{C}, V_{GE}=15\text{V}, I_C=5\text{A}, R_g=60\Omega$ )

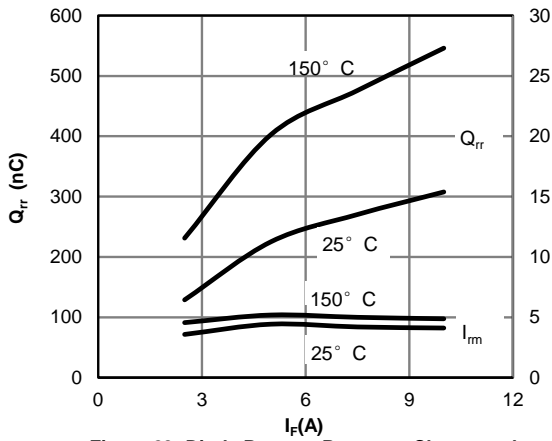
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



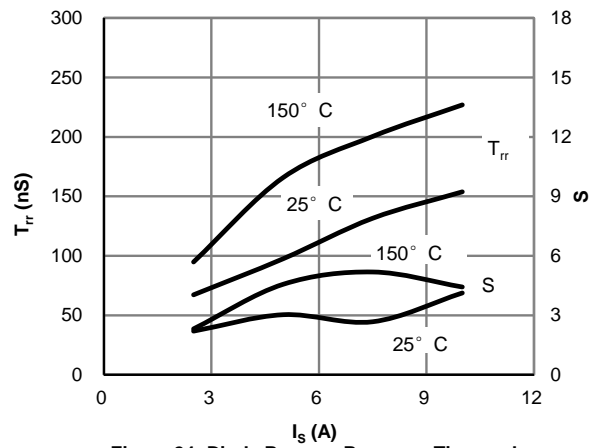
**Figure 21: Diode Reverse Leakage Current vs. Junction Temperature**



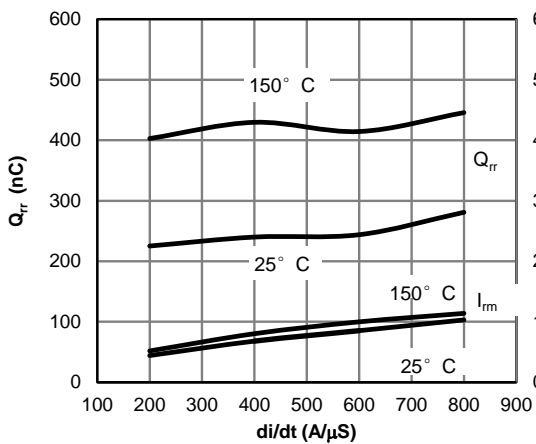
**Figure 22: Diode Forward voltage vs. Junction Temperature**



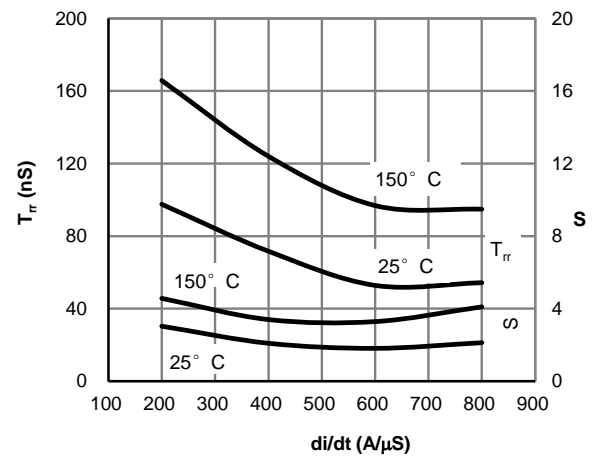
**Figure 23: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current**  
( $V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$ )



**Figure 24: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current**  
( $V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$ )

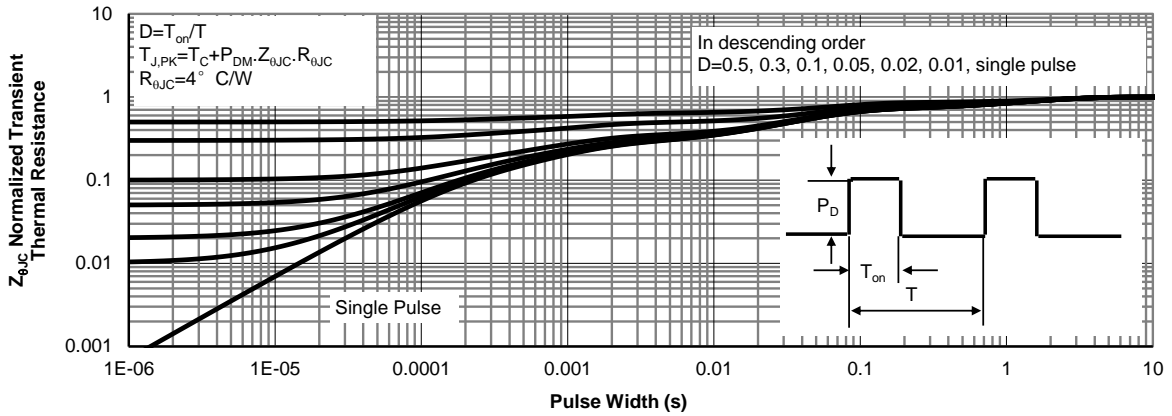


**Figure 25: Diode Reverse Recovery Charge and Peak Current vs. di/dt**  
( $V_{GE}=15V, V_{CE}=400V, I_F=5A$ )

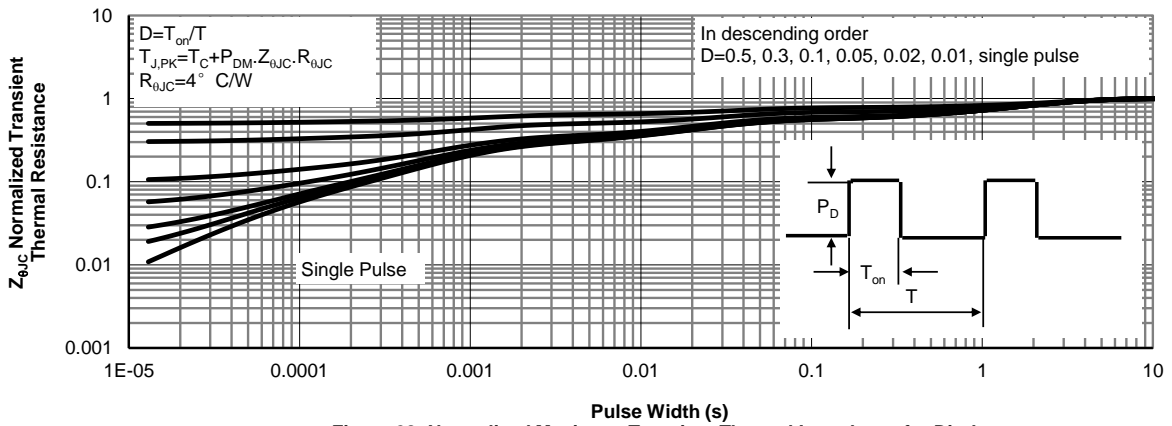


**Figure 26: Diode Reverse Recovery Time and Softness Factor vs. di/dt**  
( $V_{GE}=15V, V_{CE}=400V, I_F=5A$ )

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



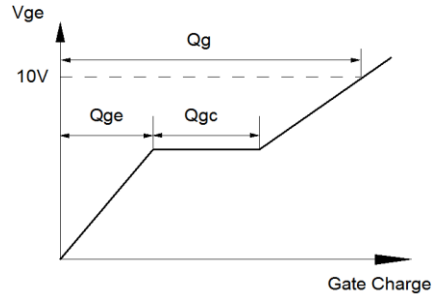
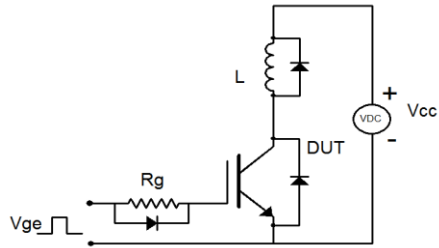
**Figure 27: Normalized Maximum Transient Thermal Impedance for IGBT**



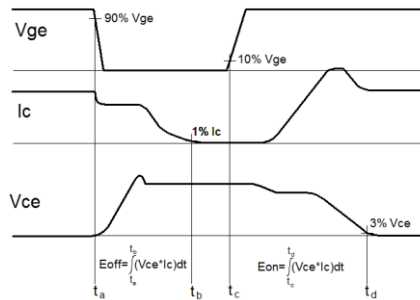
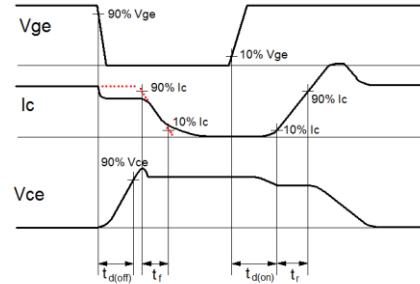
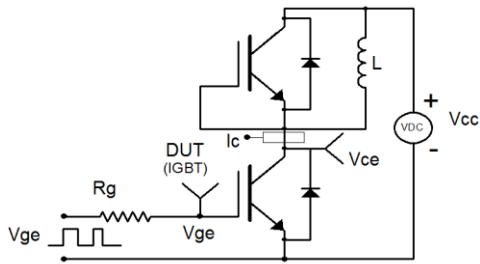
**Figure 28: Normalized Maximum Transient Thermal Impedance for Diode**



**Gate Charge Test Circuit & Waveform**



**Inductive Switching Test Circuit & Waveforms**



**Diode Recovery Test Circuit & Waveforms**

